

<b>SANYO</b>	No.4753	<b>2SK2260</b>
		N-Channel Silicon MOSFET Very High-Speed Switching Applications

**Features**

- Low ON resistance
- Very high-speed switching
- Low-voltage drive

**Absolute Maximum Ratings at Ta = 25°C**

Drain-to-Source Voltage	$V_{DSS}$	150		unit
Gate-to-Source Voltage	$V_{GSS}$	$\pm 20$		V
Drain Current(DC)	$I_D$	1.2		A
Drain Current(Pulse)	$I_{DP}$	4.8		A
Allowable Power Dissipation	$P_D$	3.5		W
		1.5		W

$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$   
 $T_c = 25^\circ C$   
Mounted on ceramic board  
(250mm<sup>2</sup> × 0.8mm)

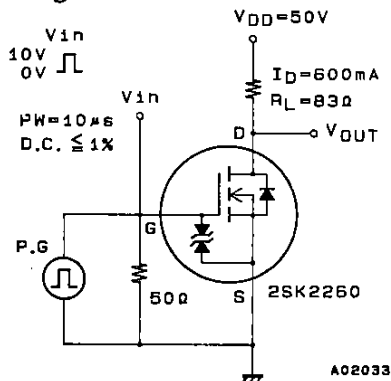
Channel Temperature	$T_{ch}$	150		°C
Storage Temperature	$T_{stg}$	- 55 to + 150		°C

**Electrical Characteristics at Ta = 25°C**

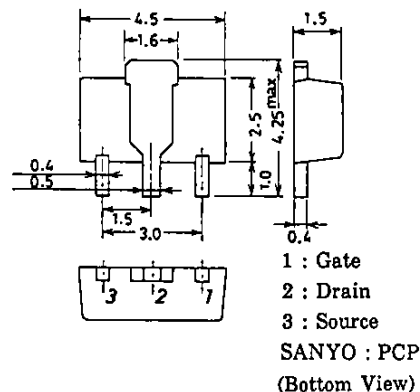
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1mA, V_{GS} = 0$	150			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 150V, V_{GS} = 0$			100	$\mu A$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 18V, V_{DS} = 0$			$\pm 10$	$\mu A$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 1mA$	1.5		2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 600mA$	0.8	1.1		S
Static Drain-to-Source On-state Resistance	$R_{DS(on)}$	$I_D = 600mA, V_{GS} = 10V$		1.6	2.2	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = 20V, f = 1MHz$		80		pF
Output Capacitance	$C_{oss}$	$V_{DS} = 20V, f = 1MHz$		25		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 20V, f = 1MHz$		8.5		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		10		ns
Rise Time	$t_r$	"		15		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		50		ns
Fall Time	$t_f$	"		30		ns
Diode Forward Voltage	$V_{SD}$	$I_S = 1.2A, V_{GS} = 0$		1.0		V

Marking : KO

**Switching Time Test Circuit**

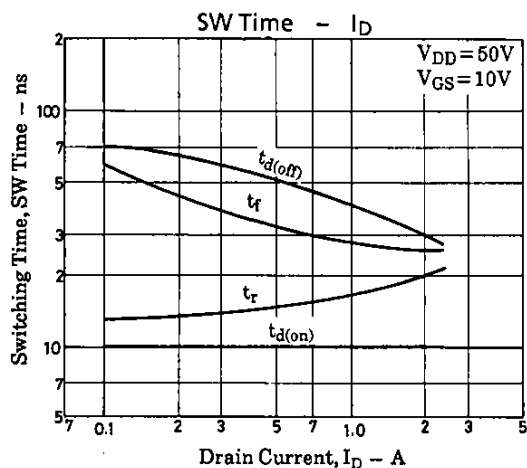
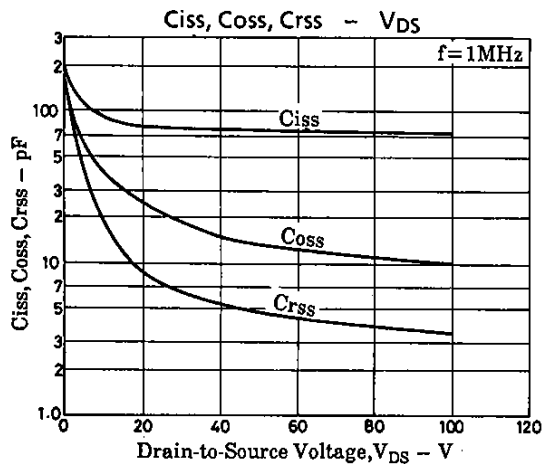
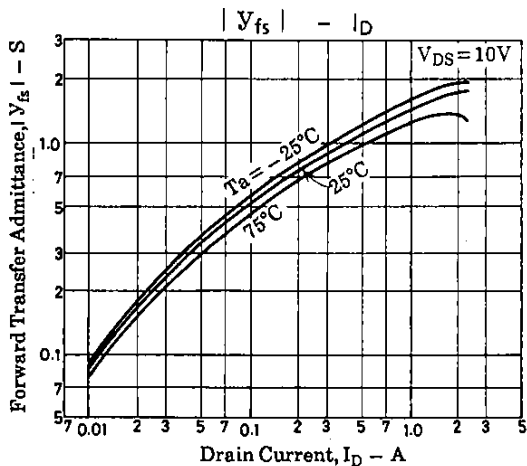
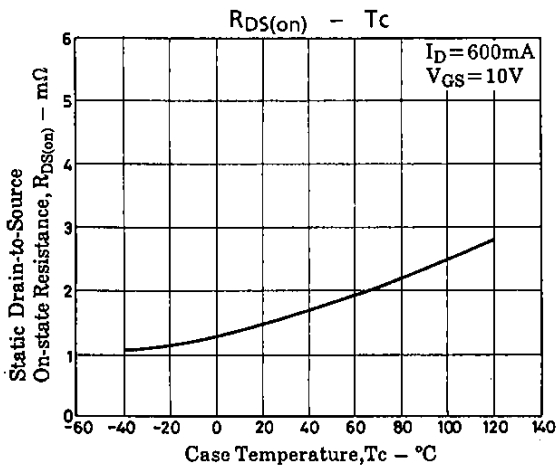
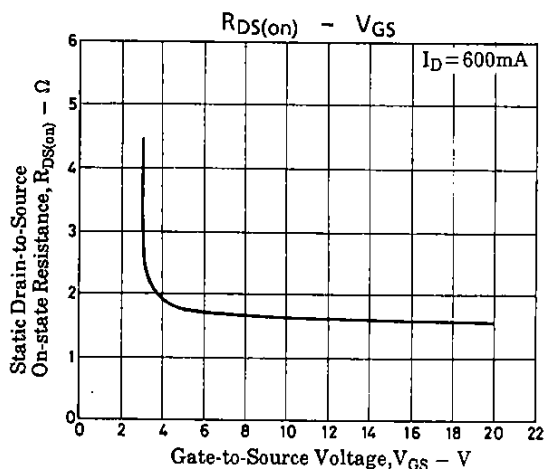
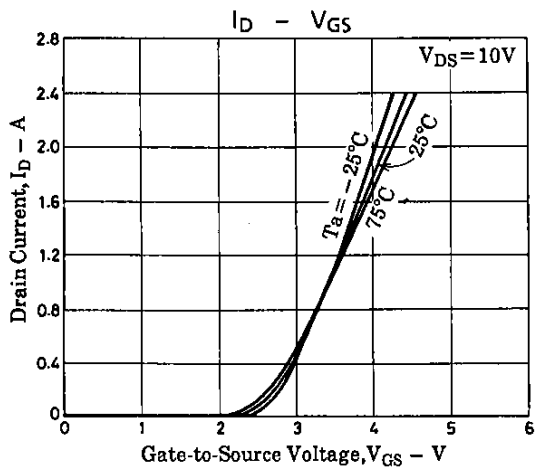
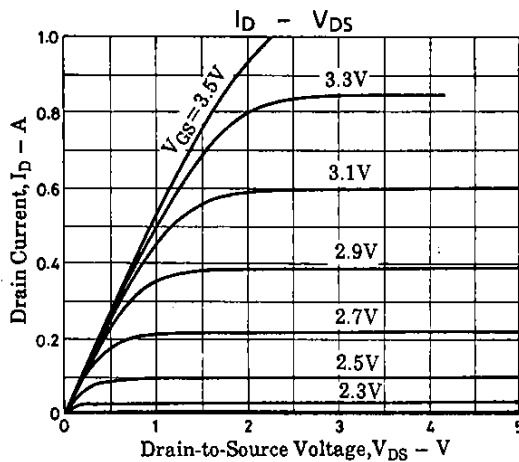
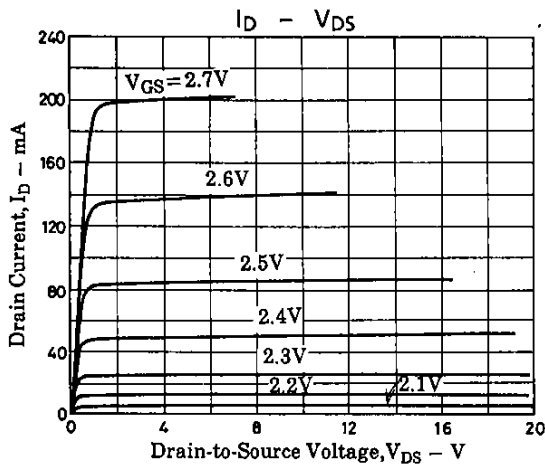


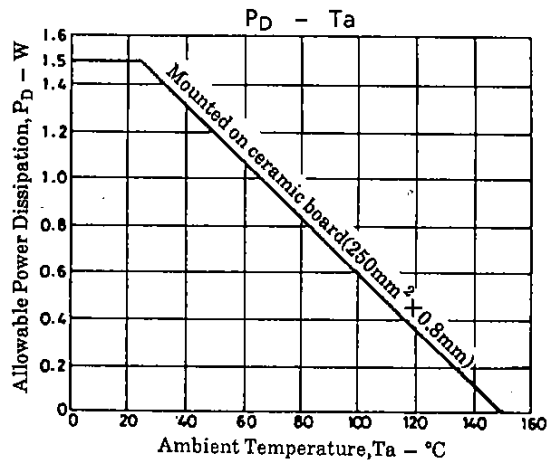
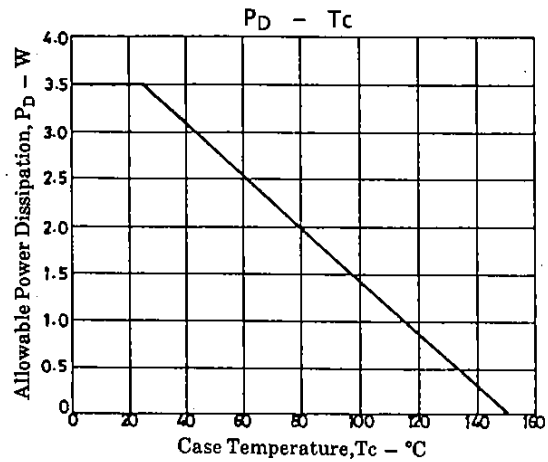
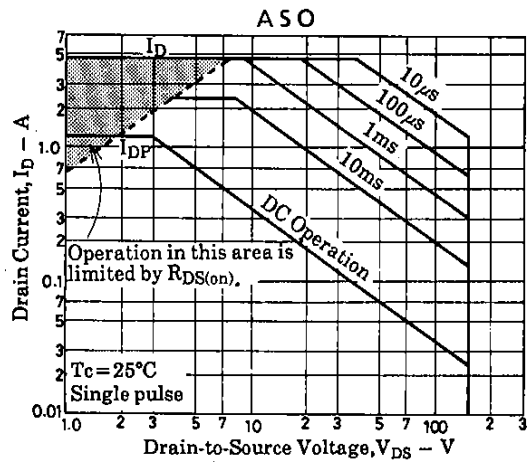
**Package Dimensions 2062A**  
(unit : mm)



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